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Heat, charge and mixed noises and their relations to thermoelectric figure of merit and differential conductances

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Thermoelectric differential conductances, as well as charge, heat and mixed noises in a mesoscopic system connected to two reservoirs are considered within the Landauer-Büttiker formalism. We deeper examine two concrete nanosystems: a quantum point contact in an ohmic environment and a quantum dot with a single energy level. In the linear response regime, we find that the figure of merit is given by the ratio between the square of the mixed noise and the product of charge and heat noises. It is also simply related to the thermoelectric differential conductances we have introduced since they are related to noises through fluctuation-dissipation theorem. In the non-linear response regime of high voltages, we find that the cross-ratio of noises calculated between left and right reservoirs can be larger than one, whereas it is limited to one when calculated within the same reservoir.

I. INTRODUCTION

The main motivation for studying thermoelectricity in quantum systems is the promise to increase the conversion efficiency by reducing the dimension. Indeed, the first measurements of values larger than one for the figure of merit were obtained in superlattices and quantum dot superlattices.[1,2] These observations were the trigger signal of a large number of both experimental and theoretical works. Increase of the thermopower has been obtained in molecular junctions between a gold substrate and a gold scanning tunneling microscope tip,[3] measurements of Seebeck coefficient have been performed in carbon nanotubes,[4,5] control break junctions,[6] magnetic tunnel junctions,[7] spin valves,[8] and Kondo quantum dots.[9] Non-linear thermovoltage and thermocurrent in quantum dot have also been highlighted.[10]

In parallel, extensive theoretical works were performed in order to understand how thermoelectrical properties are affected in nanosystems with multi channels,[11] multi-terminals,[12] on-site interaction,[13] inelastic scattering,[14,15] and time-dependent voltage.[16,17] Besides, the validity of Onsager relation linking Seebeck and Peltier coefficients, the validity of Wiedemann-Franz and Fourier laws were questioned in nanosystems.[12,18–20] Recently, the breakdown of thermoelectric reciprocity relations has been experimentally observed in a four-terminals mesoscopic device.[21]

A key point for thermoelectricity in nanosystems is the fact that the tools used to quantifies the efficiency for classical systems fail to describe the quantum ones. In particular, the figure of merit is a concept which makes sense only in the linear response regime. Indeed, the optimization of the figure of merit in nanosystems does not guarantee the optimization of efficiency.[22] Thus, one has rather to consider directly the efficiency, and look for the optimization of the ratio between electric and heat powers.[23] An other witness of the thermoelectrical conversion is the signal to noise ratio. Interest in heat noise in quantum systems and its relation to thermoelectrical conversion is currently growing up. However, these studies are mainly restricted to correlations between heat current and itself.[24–27] It is only recently that the correlations between heat and charge currents have been considered[28,29] and that the ratio between the different kinds of noises has been introduced.[30]

In this work, we have studied the heat, charge and mixed noises in a mesoscopic system connected to two reservoirs. From the Landauer-Büttiker formalism[31] we have expressed these noises in terms of thermoelectric differential conductances. It allows us to study the noises in the entire ranges of temperature, voltage and coupling to environment or reservoirs. We have first focused on the high temperature regime with equal left and right temperatures, which is linear, and second on the high voltage regime. In each of these two regimes, we have derived analytic expressions of the noises, differential conductances and study their possible relationships.

In the linear response regime, we recover the fluctuation-dissipation theorems which link electrical and thermal conductances to the charge and heat noises. In addition, we demonstrate that fluctuation-dissipation theorem also applies for mixed noises provided one considers the *new* thermoelectric conductances we have introduced. As a consequence, the figure of merit can be expressed as the ratio between the square of mixed noise and the product of heat and charge noises.

In the non-linear response regime with voltage, we were guided to distinguish between two ratios of noises: the cross-ratio that is defined between two different reservoirs and the auto-ratio defined inside a single reservoir. We moreover specify the expressions of differential conductances and noises and give their limit values in two concrete nanosystems: a quantum point contact (QPC) connected to a resistance and a quantum dot (QD) with a single energy level. Significantly, we find that in the two nanosystems the cross-ratio can reach larger values than one, while the auto-ratio cannot exceed one.

The paper is organized as follows: in Sec. II, we define

all the quantities we are interested in, i.e. differential conductances, current noises at zero frequency and ratios of noises. We give the general expressions of these quantities obtained in the framework of Landauer-Büttiker scattering theory in Sec. III, and their reduced expressions in both high temperature and high voltage regimes in Sec. IV. In Secs. V and VI, we apply our results to a QPC and a QD and discuss various regimes. We conclude in Sec. VII.

II. DEFINITIONS

We define the following zero-frequency current correlators between the reservoirs p and q:

$$\mathcal{S}_{pq}^{\alpha\beta} \;=\; \int \langle \delta\hat{I}_p^{\alpha}(t)\delta\hat{I}_q^{\beta}(0)\rangle dt \;, \tag{1}$$

where $\delta\hat{I}_p^{\alpha}(t) = \hat{I}_p^{\alpha}(t) - \langle\hat{I}_p^{\alpha}\rangle$, with $\hat{I}_p^{e(h)}$ the charge (heat) current operator, and $\langle\hat{I}_p^{e(h)}\rangle$ the charge (heat) average current in the reservoir p. $\mathcal{S}_{pq}^{ee}$ corresponds to the charge noise and $\mathcal{S}_{pq}^{hh}$ corresponds to the heat noise, whereas $\mathcal{S}_{pq}^{eh}$ and $\mathcal{S}_{pq}^{he}$ correspond to the correlations between charge and heat currents. We call them *mixed* noises. In the following, we restrict our work to two terminal systems, *i.e.* $\{p,q\} \in \{L,R\}$, where L (R) refers to the left (right) reservoir. As a general rule, we call *auto*-quantities when calculated for $p = q$, and *cross*-quantities when calculated for $p \neq q$.

To treat the non-linear response regime, we introduce differential conductances defined as:

$$G_{L,R} \;=\; \frac{\partial I_{L,R}^{e}}{\partial V_{L,R}} \;, \quad K_{R,L} = -\frac{\partial I_{L,R}^{h}}{\partial T_{R,L}} \;, \tag{2}$$

$$X_{L,R} \;=\; \frac{\partial I_{L,R}^{e}}{\partial T_{L,R}} \;, \quad Y_{R,L} = -\frac{\partial I_{L,R}^{h}}{\partial V_{R,L}} \;. \tag{3}$$

$G_{L,R}$ correspond to the electric differential conductance, $K_{R,L}$ correspond to the thermal differential conductance, whereas $X_{L,R}$ and $Y_{L,R}$ are "new" differential conductances that locally reflect the thermoelectric conversion. In the linear response regime, these two last conductances are related to Seebeck and Peltier coefficients (see Sec. IV A). We will also use average conductances merely defined as: $G = (G_L + G_R)/2$, $X = (X_L + X_R)/2$, $Y = (Y_L + Y_R)/2$, and $K = (K_L + K_R)/2$.

To probe connections between differential coefficients and noises, we introduce a dimensionless quantity: the ratio between the product of mixed correlations on the one hand, and the product of charge and heat ones on the other hand:

$$r_{pq} \;=\; \frac{\mathcal{S}_{pq}^{eh}\mathcal{S}_{pq}^{he}}{\mathcal{S}_{pq}^{ee}\mathcal{S}_{pq}^{hh}} \;. \tag{4}$$

Whereas $r_{pp} \leq 1$ because of Cauchy-Schwarz inequality, we will show here that no such limitation applies for $r_{p\neq q}$.

III. LANDAUER-*LIKE* EXPRESSIONS

We derive the formal expressions of the differential conductances, and heat, charge and mixed noises at zero frequency within the Landauer-Büttiker scattering theory.[31] We assume that the transmission coefficient $\mathcal{T}$ through the mesoscopic conductor does not depend on the external variables $V_{L,R}$ and $T_{L,R}$.

A. Differential conductances

To get the differential conductances, we use the Landauer expressions of charge and heat currents:

$$I_{L,R}^{e} \;=\; \pm\frac{e}{h}\int_{-\infty}^{\infty}\left[f_L(\epsilon) - f_R(\epsilon)\right]\mathcal{T}(\epsilon)d\epsilon \;, \tag{5}$$

$$I_{L,R}^{h} \;=\; \pm\frac{1}{h}\int_{-\infty}^{\infty}(\epsilon - eV_{L,R})\left[f_L(\epsilon) - f_R(\epsilon)\right]\mathcal{T}(\epsilon)d\epsilon \;, \tag{6}$$

where $f_p(\epsilon) = \left[1 + e^{(\epsilon - eV_p)/(k_BT_p)}\right]^{-1}$ is the Fermi-Dirac distribution function. The calculation of their derivatives according to $V_{L,R}$ or $T_{L,R}$ leads to:

$$G_{L,R} \;=\; \frac{e^2}{hk_BT_{L,R}}\int_{-\infty}^{\infty} f_{L,R}(\epsilon)[1 - f_{L,R}(\epsilon)]\mathcal{T}(\epsilon)d\epsilon \;, \tag{7}$$

$$X_{L,R} \;=\; \frac{e}{hk_BT_{L,R}^2}\int_{-\infty}^{\infty}(\epsilon - eV_{L,R}) \times f_{L,R}(\epsilon)[1 - f_{L,R}(\epsilon)]\mathcal{T}(\epsilon)d\epsilon \;, \tag{8}$$

$$Y_{R,L} \;=\; \frac{e}{hk_BT_{R,L}}\int_{-\infty}^{\infty}(\epsilon - eV_{L,R}) \times f_{R,L}(\epsilon)[1 - f_{R,L}(\epsilon)]\mathcal{T}(\epsilon)d\epsilon \;, \tag{9}$$

and,

$$K_{R,L} \;=\; \frac{1}{hk_BT_{R,L}^2}\int_{-\infty}^{\infty}(\epsilon - eV_L)(\epsilon - eV_R) \times f_{R,L}(\epsilon)[1 - f_{R,L}(\epsilon)]\mathcal{T}(\epsilon)d\epsilon \;. \tag{10}$$

These conductances obey the relation $Y_{R,L} = X_{R,L}T_{R,L} \pm (V_L - V_R)G_{R,L}$ which reduces to $Y_{R,L} = X_{R,L}T_{R,L}$ in the linear response regime (Onsager relation).

B. Current noises

Within the Landauer-Büttiker scattering theory,[31] the zero-frequency charge, charge-heat and heat currents noises are given by:

$$\mathcal{S}_{pq}^{ee} \;=\; (2\delta_{pq} - 1)\frac{e^2}{h}\int_{-\infty}^{\infty}\mathcal{F}(\epsilon)d\epsilon \;, \tag{11}$$

$$\mathcal{S}^{eh}_{pq} = (2\delta_{pq}-1)\frac{e}{h}\int_{-\infty}^{\infty}(\epsilon - eV_q)\mathcal{F}(\epsilon)d\epsilon \ , \quad (12)$$

$$\mathcal{S}^{he}_{pq} = (2\delta_{pq}-1)\frac{e}{h}\int_{-\infty}^{\infty}(\epsilon - eV_p)\mathcal{F}(\epsilon)d\epsilon \ , \quad (13)$$

and,

$$\mathcal{S}^{hh}_{pq} = (2\delta_{pq}-1)\frac{1}{h}\int_{-\infty}^{\infty}(\epsilon - eV_p)(\epsilon - eV_q)\mathcal{F}(\epsilon)d\epsilon \ , \quad (14)$$

where

$$\begin{aligned}\mathcal{F}(\epsilon) &= \mathcal{T}(\epsilon)\left[f_L(\epsilon)[1-f_L(\epsilon)] + f_R(\epsilon)[1-f_R(\epsilon)]\right] \\ &\quad +\mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)][f_L(\epsilon)-f_R(\epsilon)]^2 \ . \quad (15)\end{aligned}$$

We remark that these correlators obey relations:

$$\mathcal{S}^{ee}_{pq} = \mathcal{S}^{ee}_{qp} \ , \quad \mathcal{S}^{ee}_{pp} = \mathcal{S}^{ee}_{\bar{p}\bar{p}} \ , \quad (16)$$

and

$$\mathcal{S}^{eh}_{pq} = \mathcal{S}^{he}_{qp} \ , \quad \mathcal{S}^{eh}_{pq} = \mathcal{S}^{he}_{pq} + (V_p - V_q)\mathcal{S}^{ee}_{pq} \ , \quad (17)$$

which reduces to $\mathcal{S}^{eh}_{pq} = \mathcal{S}^{he}_{pq} = \mathcal{S}^{he}_{qp}$ in the linear response regime. Similarly:

$$\mathcal{S}^{eh}_{pp} = \mathcal{S}^{eh}_{\bar{p}\bar{p}} + (V_{\bar{p}} - V_p)\mathcal{S}^{ee}_{\bar{p}\bar{p}} \ , \quad (18)$$

which reduces to $\mathcal{S}^{eh}_{pp} = \mathcal{S}^{eh}_{\bar{p}\bar{p}}$ in the linear response regime, and

$$\mathcal{S}^{hh}_{pq} = \mathcal{S}^{hh}_{qp} \ , \quad (19)$$

$$\mathcal{S}^{hh}_{pp} = \mathcal{S}^{hh}_{\bar{p}\bar{p}} + 2(V_{\bar{p}} - V_p)\mathcal{S}^{eh}_{\bar{p}\bar{p}} + (V_{\bar{p}} - V_p)^2\mathcal{S}^{ee}_{\bar{p}\bar{p}} \ , \quad (20)$$

which reduces to $\mathcal{S}^{hh}_{pp} = \mathcal{S}^{hh}_{\bar{p}\bar{p}}$ in the linear response regime, where $\bar{p} = L$ when $p = R$, and $\bar{p} = R$ when $p = L$. As a major consequence of these relations, we conclude that the cross-ratio defined by Eq. (4) in between the two reservoirs is symmetric: $r_{RL} = r_{LR}$, thus we will not discuss $\mathcal{S}^{\alpha\beta}_{RL}$, nor r_{RL} in the paper. Inversely, r_{LL} and r_{RR} can be different as we will observe in the QD nanosystem.

C. Relations between noises and differential conductances

We want to express noises in terms of differential conductance defined in Sec. II. Reporting Eqs. (7), (8), (9) and (10) in the expressions of the charge, mixed and heat correlators given by Eqs. (11), (12), (13), and (14), we get:

$$\mathcal{S}^{ee}_{pq} = (2\delta_{pq}-1)[k_BT_LG_L + k_BT_RG_R] + (2\delta_{pq}-1)\frac{e^2}{h}\int_{-\infty}^{\infty}\mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)][f_L(\epsilon)-f_R(\epsilon)]^2d\epsilon \ , \quad (21)$$

$$\mathcal{S}^{eh}_{pq} = (2\delta_{pq}-1)[k_BT_q^2X_q + k_BT_{\bar{q}}Y_{\bar{q}}] + (2\delta_{pq}-1)\frac{e}{h}\int_{-\infty}^{\infty}(\epsilon - eV_q)\mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)][f_L(\epsilon)-f_R(\epsilon)]^2d\epsilon \ , \quad (22)$$

$$\mathcal{S}^{he}_{pq} = (2\delta_{pq}-1)[k_BT_p^2X_p + k_BT_{\bar{p}}Y_{\bar{p}}] + (2\delta_{pq}-1)\frac{e}{h}\int_{-\infty}^{\infty}(\epsilon - eV_p)\mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)][f_L(\epsilon)-f_R(\epsilon)]^2d\epsilon \ , \quad (23)$$

$$\begin{aligned}\mathcal{S}^{hh}_{pq} &= (2\delta_{pq}-1)[k_BT_L^2K_L + k_BT_R^2K_R] + \delta_{pq}(V_{\bar{p}} - V_p)[k_BT_p^2X_p + k_BT_{\bar{p}}Y_{\bar{p}}]/e \\ &\quad +(2\delta_{pq}-1)\frac{1}{h}\int_{-\infty}^{\infty}(\epsilon - eV_p)(\epsilon - eV_q)\mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)][f_L(\epsilon)-f_R(\epsilon)]^2d\epsilon \ . \quad (24)\end{aligned}$$

With the help of these relations, we can discuss in a quite direct way the behaviors of noises in various regimes as done in the next section.

IV. HIGH TEMPERATURE AND HIGH VOLTAGE REGIMES

We now specify $V_{L,R}$ and $T_{L,R}$ in terms of voltage gradient, V, and temperature gradient, T, between the reservoirs: $V_{L,R} = \pm V/2$ and $T_{L,R} = T_0 \pm T/2$, where T_0 is the average temperature.

A. High temperature regime ($k_BT_0 \gg eV$)

In that regime, the last contributions in Eqs. (21), (22), (23) and (24) are negligible, thus we can write these for-

mula in terms of differential conductances. We find:

$$\mathcal{S}^{ee}_{LL} = \mathcal{S}^{ee}_{RR} = k_B T_L G_L + k_B T_R G_R = -\mathcal{S}^{ee}_{LR} \ , \quad (25)$$
$$\mathcal{S}^{eh}_{LL} = \mathcal{S}^{he}_{LL} = k_B T_L^2 X_L + k_B T_R Y_R = -\mathcal{S}^{he}_{LR} \ , \quad (26)$$
$$\mathcal{S}^{eh}_{RR} = \mathcal{S}^{he}_{RR} = k_B T_R^2 X_R + k_B T_L Y_L = -\mathcal{S}^{eh}_{LR} \ , \quad (27)$$
$$\mathcal{S}^{hh}_{LL} = \mathcal{S}^{hh}_{RR} = k_B T_L^2 K_L + k_B T_R^2 K_R = -\mathcal{S}^{hh}_{LR} \ . \quad (28)$$

We remark that auto- and cross-correlations have the same absolute value. In addition, from Eqs. (12) and (13), it can be seen that $\mathcal{S}^{eh}_{LL} = \mathcal{S}^{eh}_{RR}$ which leads to $T_L^2 X_L + T_R Y_R = T_R^2 X_R + T_L Y_L$, in full agreement with the Onsager relation $Y_{L,R} = T_{L,R} X_{L,R}$. For equal left and right temperatures, i.e. T go the zero, we are back to the linear response regime which gives $Y = XT_0$ as already mentioned in Sec. III.A., and the noises simplify to:

$$\mathcal{S}^{ee}_{LL} = \mathcal{S}^{ee}_{RR} = 2k_B T_0 G = -\mathcal{S}^{ee}_{LR} \ , \quad (29)$$
$$\mathcal{S}^{eh}_{LL} = \mathcal{S}^{eh}_{RR} = 2k_B T_0^2 X = -\mathcal{S}^{he}_{LR} \ , \quad (30)$$
$$\mathcal{S}^{he}_{LL} = \mathcal{S}^{he}_{RR} = 2k_B T_0 Y = -\mathcal{S}^{eh}_{LR} \ , \quad (31)$$
$$\mathcal{S}^{hh}_{LL} = \mathcal{S}^{hh}_{RR} = 2k_B T_0^2 K = -\mathcal{S}^{hh}_{LR} \ . \quad (32)$$

Eqs. (29) and (32) correspond to the fluctuation-dissipation theorem for the charge and heat noises respectively. We find here that it exists also direct links between mixed noises and thermoelectrical conductances X and Y given by Eqs. (30) and (31).

From Eqs. (29), (30), (31) and (32), we directly deduced that all auto- and cross-ratios are identical in the linear limit:

$$r_{LL} = r_{RR} = r_{LR} \ . \quad (33)$$

In addition, it can been shown that X and Y are related to the Seebeck S and Peltier Π coefficients through the relations:

$$X = -GS \ , \quad (34)$$
$$Y = -\Pi G = -ST_0 G \ . \quad (35)$$

With the help of these results, the thermoelectric figure of merit, given by $ZT_0 = S^2 T_0 G/K$, can be fully expressed either in terms of differential conductances, or in terms of the noises defined in Sec. II. Indeed, from Eqs. (29) to (35), we have:

$$ZT_0 = \frac{XY}{GK} = \frac{S^{eh}_{pq} S^{he}_{pq}}{S^{ee}_{pq} S^{hh}_{pq}} = r_{pq} \ , \quad (36)$$

which is verified whatever are the choice of the reservoirs p and q. Thus, in the linear response regime, the figure of merit for thermoelectricity corresponds to the ratio between the product of mixed noises and the product of heat and charge noises. This ratio is hence relevant to quantify the efficiency of thermoelectric conversion. This relation is an important result of this paper.

B. High voltage regime ($eV \gg k_B T_0$)

In that regime, the first and second contributions in Eqs. (21), (22), (23) and (24) are negligible and we set $T_{L,R}$ to zero, thus:

$$\mathcal{S}^{ee}_{LL} = \frac{e^2}{h}\mathrm{sign}(V) \int_{-eV/2}^{eV/2} \mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)]d\epsilon = -\mathcal{S}^{ee}_{LR} \ , \quad (37)$$
$$\mathcal{S}^{eh}_{LL} = \frac{e}{h}\mathrm{sign}(V) \int_{-eV/2}^{eV/2} \left(\epsilon - \frac{eV}{2}\right) \mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)]d\epsilon = -\mathcal{S}^{he}_{LR} \ , \quad (38)$$
$$\mathcal{S}^{he}_{RR} = \frac{e}{h}\mathrm{sign}(V) \int_{-eV/2}^{eV/2} \left(\epsilon + \frac{eV}{2}\right) \mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)]d\epsilon = -\mathcal{S}^{eh}_{LR} \ , \quad (39)$$
$$\mathcal{S}^{hh}_{LL} = \frac{1}{h}\mathrm{sign}(V) \int_{-eV/2}^{eV/2} \left(\epsilon - \frac{eV}{2}\right)^2 \mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)]d\epsilon \ , \quad (40)$$
$$\mathcal{S}^{hh}_{RR} = \frac{1}{h}\mathrm{sign}(V) \int_{-eV/2}^{eV/2} \left(\epsilon + \frac{eV}{2}\right)^2 \mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)]d\epsilon \ , \quad (41)$$
$$\mathcal{S}^{hh}_{LR} = -\frac{1}{h}\mathrm{sign}(V) \int_{-eV/2}^{eV/2} \left(\epsilon^2 - \frac{e^2V^2}{4}\right) \mathcal{T}(\epsilon)[1-\mathcal{T}(\epsilon)]d\epsilon \ . \quad (42)$$

Contrary to what happens in the high temperature regime, the heat auto- and cross-correlators take here distinct values.

We now focus on two concrete nanosystems namely a quantum point contact and a quantum dot to further examine theses correlators and the ratios of noises we

have introduced.

V. APPLICATION TO A QUANTUM POINT CONTACT

The first application of our results concerns a quantum point contact in an ohmic environment whose resistance is equal to $R_Q = h/e^2$ (see Fig. 1). Because of this coupling with environment, measured by Γ, its transmission coefficient acquires an energy dependency: $\mathcal{T}(\epsilon) = \epsilon^2/(\epsilon^2 + \Gamma^2)$. This energy dependency is obtained by using a mapping between this system and a Luttinger liquid with a single impurity and interactions parameter equal to one half[32–35] allowing us to perform a refermionization procedure.[36,37] Since this system exhibits an electron-hole symmetry, the thermoelectric differential conductances X and Y are equal to zero. We will show that is also the case of the mixed noises $\mathcal{S}^{eh}_{pq}$ and $\mathcal{S}^{he}_{pq}$ in the high temperature regime but not in the high voltage regime.

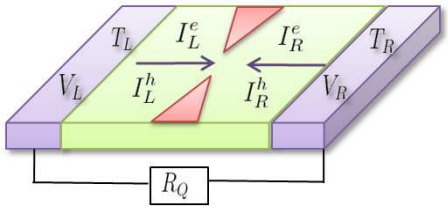

FIG. 1: Picture of the QPC coupled with an ohmic environment, and conventions chosen for left/right currents.

QPC	$\{eV, \Gamma\} \ll k_B T_0$	$eV \ll k_B T_0 \ll \Gamma$
G	G_Q	$\frac{\pi^2}{3}\left(\frac{k_B T_0}{\Gamma}\right)^2 G_Q$
X, Y	0	0
K	K_Q	$\frac{7\pi^2}{5}\left(\frac{k_B T_0}{\Gamma}\right)^2 K_Q$
$\mathcal{S}^{ee}_{LL} = -\mathcal{S}^{ee}_{LR} = 2k_B T_0 G$	$2k_B T_0 G_Q$	$\frac{2\pi^2}{3}\frac{(k_B T_0)^3}{\Gamma^2} G_Q$
$\mathcal{S}^{eh}_{LL} = -\mathcal{S}^{he}_{LR} = 2k_B T_0 Y$	0	0
$\mathcal{S}^{hh}_{LL} = -\mathcal{S}^{hh}_{LR} = 2k_B T_0^2 K$	$2k_B T_0^2 K_Q$	$\frac{14\pi^2}{5}\frac{k_B^3 T_0^4}{\Gamma^2} K_Q$
$r_{LL} = r_{RR} = r_{LR}$	0	0

TABLE I: High temperature regime in a QPC: equivalent expressions of the differential conductances, noises and ratios of noises obtained for $V = 0$ and $T_{L,R} = T_0$. $G_Q = e^2/h$ is the quantum of electrical conductance, and $K_Q = \pi^2 k_B^2 T_0/3h$ is the quantum of thermal conductance.[38]

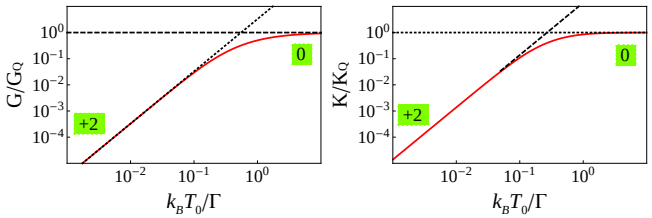

FIG. 2: High temperature regime in a QPC: differential conductances G and K as a function of the average temperature T_0 for $V = 0$ and $T = 0$. X and Y are not shown since they are equal to zero in this regime. As a consequence, the associated ratios r_{pq} of noises cancel. The exponents of the power law obtained in the asymptotic limits are indicated by the green squares.

A. High temperature regime ($k_B T_0 \gg eV$)

We first focus on the case where the temperatures of the reservoirs are identical and large in comparison to the applied voltage. Since X and Y are equal to zero, but not G and K (see Tab. I), the resulting figure of merit, such as the ratio of noises, cancel because of Eq. (36). Noises are deduced from Eqs. (29), (30), (31) and (32) and their equivalent expressions are given in Tab. I.

Figure 2 shows the crossover between the power law behavior of the differential conductances G and K at strong coupling Γ with the environment and their constant asymptotic limits G_Q and K_Q at weak Γ which corresponds to a decoupled QPC from the ohmic environment.

B. High voltage regime ($eV \gg k_B T_0$)

We now turn our interest to the case where applied voltage is large in comparison to temperature. In that limit, the integrals of Eqs. (37), (38), (39), (40), (41) and (42) can be performed analytically (see Appendix A for the expressions of the noises). The asymptotic expressions of the differential conductances, noises and ratios of noises are given in Tab. II. Only the electrical conductance is relevant in this regime: $X = Y = K = 0$. We see that G does not depend on voltage when eV is the greatest energy of the problem (central column of Tab. II).

The charge and heat noises in the same reservoirs, $\mathcal{S}^{ee}_{LL}$ and $\mathcal{S}^{hh}_{LL}$, stay positive whereas the mixed noises, $\mathcal{S}^{eh}_{LL}$ and $\mathcal{S}^{he}_{LL}$, can take negative values. The charge noise between distinct reservoirs, $\mathcal{S}^{ee}_{LR}$, has a negative sign but $\mathcal{S}^{hh}_{LR}$ stays positive. From Eqs. (40) and (41), we confirm that in the high voltage limit $\mathcal{S}^{hh}_{LL} = \mathcal{S}^{hh}_{RR}$ due to the parity of the QPC transmission $\mathcal{T}(\epsilon)$. This property ensures identical auto-ratios: $r_{LL} = r_{RR}$. Comparing central and last columns of Tab. II, we remark that $\mathcal{S}^{eh}_{LL} = -(V/2)\mathcal{S}^{ee}_{LL}$ and $\mathcal{S}^{hh}_{LL} \propto -(V/2)\mathcal{S}^{eh}_{LL}$ (idem for the cross-noises). The proportionality coefficient is exactly 1 when $\{k_B T_0, \Gamma\} \ll eV$, while for $k_B T_0 \ll eV \ll \Gamma$, it is

above one (8/5) for the auto-noises and below 1 (2/5) for the cross-noises, which conducts to $r_{LL} < 1$ and $r_{LR} > 1$ respectively (see central and last columns of Tab. IV).

QPC	$\{k_BT_0, \Gamma\} \ll eV$	$k_BT_0 \ll eV \ll \Gamma$
G	G_Q	$\left(\frac{eV}{2\Gamma}\right)^2 G_Q$
X, Y, K	0	0
$\mathcal{S}^{ee}_{LL} = -\mathcal{S}^{ee}_{LR}$	$\frac{\pi\Gamma}{2}G_Q$	$\frac{e^3\lvert V\rvert^3}{12\Gamma^2}G_Q = \frac{e\lvert V\rvert}{3}G$
$\mathcal{S}^{eh}_{LL} = -\mathcal{S}^{eh}_{RR}$ $= -\mathcal{S}^{he}_{LR}$	$-\frac{\pi\Gamma V}{4}G_Q = -\frac{V}{2}\mathcal{S}^{ee}_{LL}$	$-\frac{e^3\lvert V\rvert^3 V}{24\Gamma^2}G_Q = -\frac{V}{2}\mathcal{S}^{ee}_{LL}$
$\mathcal{S}^{hh}_{LL}$	$\frac{\pi\Gamma V^2}{8}G_Q = \frac{V^2}{4}\mathcal{S}^{ee}_{LL}$	$\frac{e^3\lvert V\rvert^5}{30\Gamma^2}G_Q = \frac{2V^2}{5}\mathcal{S}^{ee}_{LL}$
$\mathcal{S}^{hh}_{LR}$	$\frac{\pi\Gamma V^2}{8}G_Q = -\frac{V^2}{4}\mathcal{S}^{ee}_{LR}$	$\frac{e^3\lvert V\rvert^5}{120\Gamma^2}G_Q = -\frac{V^2}{10}\mathcal{S}^{ee}_{LR}$
$r_{LL} = r_{RR}$	1	5/8
r_{LR}	1	5/2

TABLE II: High voltage regime in a QPC: equivalent expressions of the differential conductances, noises and ratios of noises obtained for $T_{L,R} = 0$.

In the left graph of Fig. 3 is shown the variation of the electrical conductance as a function of voltage. By comparing the last columns of Tabs. I and II, we notice that the power law exponent obtained in the limit $k_BT_0 \ll eV \ll \Gamma$, for which we have $G \propto (eV/\Gamma)^2$, is the same than the one obtained in the limit $eV \ll k_BT_0 \ll \Gamma$ for which we have $G \propto (k_BT_0/\Gamma)^2$, meaning that temperature and voltage play a similar role for electrical conductance.[39] It is not the case for thermal conductance K for which we found that it vanishes in the high voltage regime, whereas it varies as a power law in the high temperature regime.

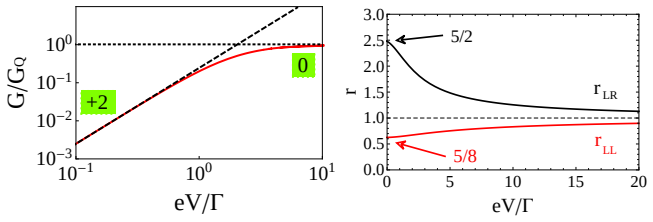

FIG. 3: High voltage regime in a QPC: (left) differential conductance G (red line) and its asymptotic power law exponents (green squares); (right) noises ratios ($r_{LL} = r_{RR}$) as a function of voltage at zero temperatures.

Contrary to what happens in the high temperature regime, the ratios of noises are non-zero in the high voltage regime. Interestingly, whereas r_{LL} stays below one when varying voltage, the cross-ratio r_{LR} exhibits a value larger than one (up to 5/2) in the strong coupling limit as shown in the right graph of Fig. 3, where equivalent expressions given in Tab. II are recovered in both $eV/\Gamma \ll 1$ and $eV/\Gamma \gg 1$ limits.

VI. APPLICATION TO A QUANTUM DOT

We now consider a single level non-interacting quantum dot with a transmission coefficient $\mathcal{T}(\epsilon) = \Gamma^2/[(\epsilon - \epsilon_0)^2 + \Gamma^2]$, where ϵ_0 is the energy level of the dot (see Fig. 4), and Γ is the broadening due to the contact to the reservoirs which is assumed to be energy independent and symmetrical $\Gamma_L = \Gamma_R = \Gamma$.

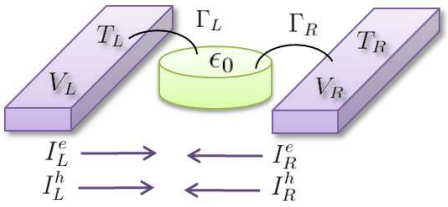

FIG. 4: Picture of the QD and conventions chosen for left/right currents.

A. High temperature regime ($k_BT_0 \gg eV$)

In Fig. 5 are plotted differential conductances as well as their asymptotic limits summarized in Table III. For both limits $k_BT_0 \ll \Gamma$ and $k_BT_0 \gg \Gamma$, these quantities exhibit a power law behavior with various exponents. Notice that X, Y, S^{eh}_{pq}, S^{he}_{pq} and r_{pq} all cancel when electron-hole symmetry applied, i.e. $\epsilon_0 = 0$, and thus we recover for the noises the results obtained in the QPC since in that case $\mathcal{T}_{\rm QD}(\epsilon) = 1 - \mathcal{T}_{\rm QPC}(\epsilon)$ (compare central column of Tab. I and last column of Tab. III).

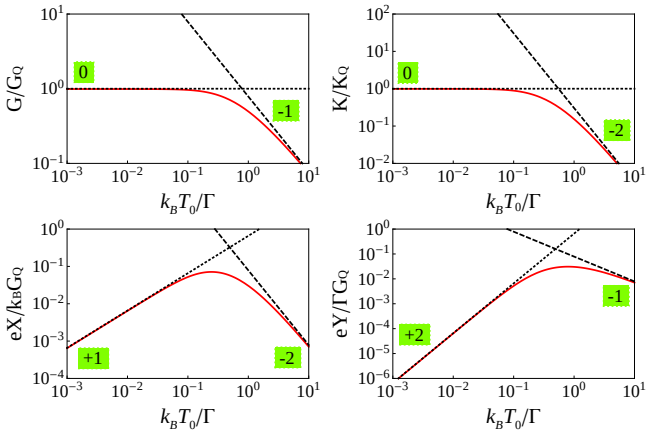

FIG. 5: High temperature regime in a QD: differential conductances as a function of average temperature for $V = 0$, $T = 0$, and $\epsilon_0/\Gamma = 0.1$.

In the high temperature regime, the ratios r_{LL} and r_{LR} are equal each other and they correspond to XY/GK since the fluctuation-dissipation theorem applies. Fig. 6 shows the evolution of these ratios as a function of T_0 and

QD	$\{eV,\Gamma\} \ll k_BT_0$	$eV \ll k_BT_0 \ll \Gamma$
G	$\frac{\pi}{4}\left(\frac{\Gamma}{k_BT_0}\right)G_Q$	G_Q
$Y = XT_0$	$\frac{\pi\epsilon_0}{4e}\left(\frac{\Gamma}{k_BT_0}\right)G_Q$	$\frac{2\pi^2\epsilon_0}{3e}\left(\frac{k_BT_0}{\Gamma}\right)^2 G_Q$
K	$\frac{3}{\pi^2}\left(\frac{\Gamma}{k_BT_0}\right)^2 K_Q$	K_Q
$\mathcal{S}^{ee}_{LL} = -\mathcal{S}^{ee}_{LR}$ $= 2k_BT_0G$	$\frac{\pi\Gamma}{2}G_Q$	$2k_BT_0G_Q$
$\mathcal{S}^{eh}_{LL} = -\mathcal{S}^{he}_{LR}$ $= 2k_BT_0Y$	$\frac{\pi\Gamma\epsilon_0}{2e}G_Q$	$\frac{4\pi^2}{3e}\left(\frac{k_BT_0}{\Gamma}\right)^3\Gamma\epsilon_0 G_Q$
$\mathcal{S}^{hh}_{LL} = -\mathcal{S}^{hh}_{LR}$ $= 2k_BT_0^2K$	$\frac{6\Gamma^2}{\pi^2k_B}K_Q$	$2k_BT_0^2K_Q$
$r_{LL} = r_{RR} = r_{LR}$	$\frac{\pi}{4}\frac{\epsilon_0^2}{\Gamma k_BT_0} = \frac{XY}{GK}$	$\frac{4\pi^2}{3}\left(\frac{k_BT_0\epsilon_0}{\Gamma^2}\right)^2 = \frac{XY}{GK}$

TABLE III: High temperature regime in a QD: equivalent expressions of the differential conductances, noises and ratios of noises obtained for $V = 0$, $T_{L,R} = T_0$, and $\varepsilon_0 \ll \Gamma$.

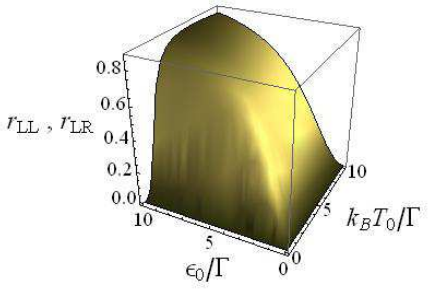

FIG. 6: QD in the high temperature regime: variation of the ratios $r_{LL} = r_{RR} = r_{LR}$ as a function of temperature T_0 and dot energy level for equal left and right temperature at zero voltage.

ϵ_0 in the absence of temperature gradient. They vanish at $\epsilon_0 = 0$ as expected and their maximum does not exceed one even for large values of ϵ_0 because of Cauchy-Schwarz inequality.

B. High voltage regime ($eV \gg k_BT_0$)

In that regime, the differential electrical conductance reads as

$$G = \frac{G_Q}{2}\sum_{\pm}\frac{\Gamma^2}{(\epsilon_0 \pm eV/2)^2 + \Gamma^2}\ , \qquad (43)$$

and we have: $K = X = Y = 0$. The integrals of Eqs. (37), (38), (39), (40), (41) and (42) are performed analytically (see Appendix B for the expressions of the noises). The equivalent expressions of conductances and noises are given in Tab. IV. As in the QPC, we find that heat, charge and mixed noises are strongly related via the voltage, since we have $\mathcal{S}^{eh}_{LL} = -(V/2)\mathcal{S}^{ee}_{LL}$ and $\mathcal{S}^{he}_{LR} = -(V/2)\mathcal{S}^{ee}_{LR}$ in all cases, and more $\mathcal{S}^{hh}_{LL} \propto -(V/2)\mathcal{S}^{eh}_{LL} \propto (V^2/4)\mathcal{S}^{ee}_{LL}$ and $\mathcal{S}^{hh}_{LR} \propto (V/2)\mathcal{S}^{he}_{LR} \propto -(V^2/4)\mathcal{S}^{ee}_{LR}$. For a strict equality, both auto- and cross-ratios of noises reach one. Otherwise, the proportionality coefficients lead to $r_{LL} < 1$ and $r_{LR} > 1$ and stay unchanged as long as eV stays the lowest energy of the problem excluding temperature (compare second and third colum ns of Tab. IV). In Tab. IV, the expressions for $\mathcal{S}^{hh}_{LL}$ and $\mathcal{S}^{hh}_{RR}$, and hence for auto-ratios, are identical in the three limits we consider. This is no longer the case in intermediate regimes, in contrast with the QPC, as shown Figs. 7 and 8. Indeed, $\mathcal{T}_{QD}(\epsilon)$ is no longer even when $\epsilon_0 \neq 0$ which leads to $\mathcal{S}^{hh}_{LL} \neq \mathcal{S}^{hh}_{RR}$.

QD	$\{eV,\Gamma\} \ll \epsilon_0$	$\{eV,\epsilon_0\} \ll \Gamma$	$\{\Gamma,\epsilon_0\} \ll eV$
G	$\frac{\Gamma^2}{\epsilon_0^2}G_Q$	G_Q	$\frac{4\Gamma^2}{e^2V^2}G_Q$
X, Y, K	0	0	0
$\mathcal{S}^{ee}_{LL} = -\mathcal{S}^{ee}_{LR}$	$(\frac{\Gamma}{\epsilon_0})^2 e\lvert V\rvert G_Q = e\lvert V\rvert G$	$(\frac{\epsilon_0}{\Gamma})^2 e\lvert V\rvert G_Q$	$\frac{\pi\Gamma}{2}G_Q = \frac{\pi e^2V^2}{2\Gamma}G$
$\mathcal{S}^{eh}_{LL} = -\mathcal{S}^{he}_{LR}$	$-(\frac{\Gamma}{\epsilon_0})^2\frac{e\lvert V\rvert}{2}G_Q = -\frac{V}{2}\mathcal{S}^{ee}_{LL}$	$-(\frac{\epsilon_0}{\Gamma})^2\frac{e\lvert V\rvert}{2}G_Q = -\frac{V}{2}\mathcal{S}^{ee}_{LL}$	$-\frac{\pi\Gamma V}{4}G_Q = -\frac{V}{2}\mathcal{S}^{ee}_{LL}$
$\mathcal{S}^{hh}_{LL} = \mathcal{S}^{hh}_{RR}$	$(\frac{\Gamma}{\epsilon_0})^2\frac{e\lvert V\rvert^3}{3}G_Q = \frac{V^2}{3}\mathcal{S}^{ee}_{LL}$	$(\frac{\epsilon_0}{\Gamma})^2\frac{e\lvert V\rvert^3}{3}G_Q = \frac{V^2}{3}\mathcal{S}^{ee}_{LL}$	$\frac{\pi\Gamma V^2}{8}G_Q = \frac{V^2}{4}\mathcal{S}^{ee}_{LL}$
$\mathcal{S}^{hh}_{LR}$	$(\frac{\Gamma}{\epsilon_0})^2\frac{e\lvert V\rvert^3}{6}G_Q = -\frac{V^2}{6}\mathcal{S}^{ee}_{LR}$	$(\frac{\epsilon_0}{\Gamma})^2\frac{e\lvert V\rvert^3}{6}G_Q = -\frac{V^2}{6}\mathcal{S}^{ee}_{LR}$	$\frac{\pi\Gamma V^2}{8}G_Q = -\frac{V^2}{4}\mathcal{S}^{ee}_{LR}$
$r_{LL} = r_{RR}$	3/4	3/4	1
r_{LR}	3/2	3/2	1

TABLE IV: High voltage regime in a QD: equivalent expressions of the differential conductances, noises and ratios of noises obtained for $T_{L,R} = 0$. We stress that auto- heat correlators and ratios reach identical expressions only in the limits reported in this table (see Figs. 7 and 8).

Comparing auto- and cross-ratios in Fig. 7, we see that they take distinct values in the high voltage regime, in opposite to what happens in the high temperature regime, because of the distinct values taken by $\mathcal{S}^{hh}_{LL}$ and $\mathcal{S}^{hh}_{LR}$. Same as for the QPC, the cross-ratio r_{LR} can have a value larger than one, whereas r_{LL} and r_{RR} stay always smaller than one, in agreement with Cauchy-Schwarz inequality. At zero voltage and non-zero ϵ_0, we recover the fractional values 3/4 for r_{LL} (r_{RR}), and 3/2 for r_{LR} as expected from Tab. IV. At both zero voltage and dot energy level, we recover the fractional values 5/8 for r_{LL} (r_{RR}), and 5/2 for r_{LR} as expected from Tab. II.

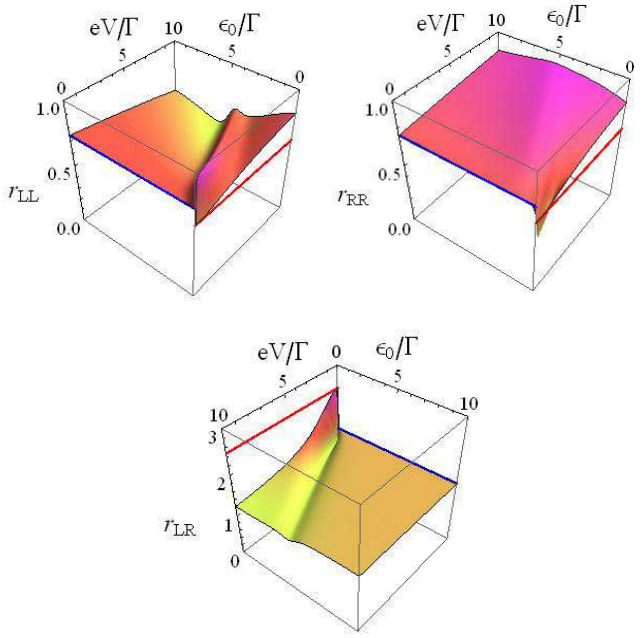

FIG. 7: QD: variation of the ratios r_{LL}, r_{RR} and r_{LR} as a function of voltage and dot energy level at zero temperatures. On both graphs, the red lines indicates their values in the limit $\epsilon_0 = eV = 0$ (i.e., $r_{LL} = r_{RR} = 5/8$ and $r_{LR} = 5/2$) and the blue lines in the limit $eV \ll \epsilon_0$ (i.e., $r_{LL} = r_{RR} = 3/4$ and $r_{LR} = 3/2$).

Finally, we plot on Fig. 8 these ratios as a function of voltage and temperature gradient: the two ratios remain almost not sensitive to temperature gradient while they vary strongly with voltage. Again, we stress that auto-ratios r_{LL} and r_{LR} are distinct in the high voltage regime of the QD. In addition, r_{LR} exhibits a divergence at a voltage value for which either $\mathcal{S}^{ee}_{LR}$ or $\mathcal{S}^{hh}_{LR}$ cancels.

VII. CONCLUSIONS

We investigated heat, charge and mixed zero-frequency noises in a mesoscopic thermoelectric systems connected to reservoirs using Landauer-Büttiker formalism. In the

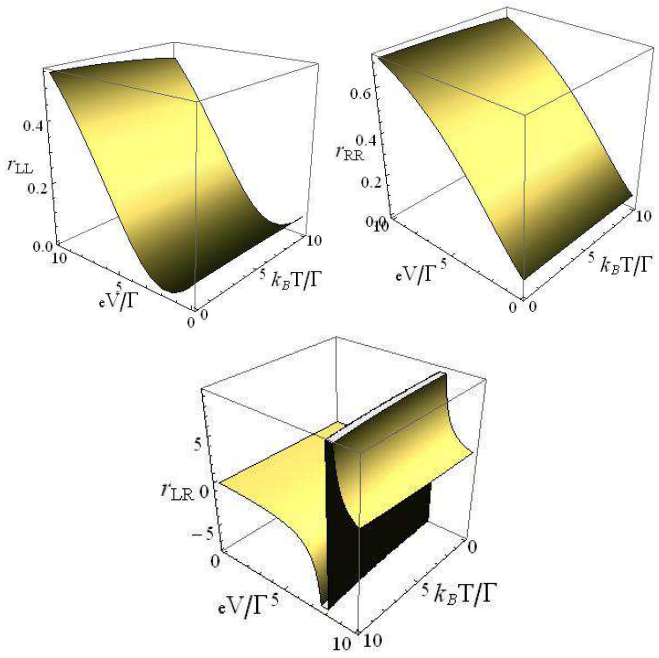

FIG. 8: QD: variation of the ratios r_{LL}, r_{RR} and r_{LR} as a function of the voltage and the temperature gradients. We take $\epsilon_0/\Gamma = 1$ and $k_B T_0/\Gamma = 10$. A divergence appears when either $\mathcal{S}^{ee}_{LR}$ or $\mathcal{S}^{hh}_{LR}$ cancels.

future perspective of studying the thermoelectric conversion, we explored two routes. On the one hand, we developed relations between the noises and thermoelectric differential conductances G, K, X and Y we defined which are the adequate quantities to consider in the non-linear regime. On the other hand, we interconnected the different noises via ratios of the product of mixed noises divided by the product of charge and heat noises, calculated inside the same reservoir (r_{LL} and r_{RR}) or in between two ($r_{LR} = r_{RL}$). The strategy was applied in the linear regime of high temperature, and in the non-linear regime of high voltage in two related nanosystems: a quantum point contact and a quantum dot. Our main conclusions follow.

From general derivations, we are able to obtain for the differential conductances and for noises analytical expressions in various limits.

In the linear response regime, we have found that X and Y are related to Seebeck and Peltier coefficients, and that the figure of merit is given by $ZT_0 = XY/GK$ since fluctuation-dissipation theorem holds. Applying our results to a QPC and a QD, we recover the fact that the differential conductances X and Y cancel for systems with electron-hole symmetry. The same applies for the mixed noises and the ratios of noises in the high temperature regime, but not in the high voltage regime. Indeed, from Tabs. II and IV, we can see that X and Y are both equal to zero when $\epsilon_0 = 0$, but not $\mathcal{S}^{eh}_{pq}$, nor r_{pq}. It allows to conclude that the ratios of noises is no longer related

to the ratio of differential conductances in the non-linear regime.

In the linear response regime, the correlations between heat and charge currents deliver indication about the efficiency of thermoelectric conversion. Indeed, we have shown that the figure of merit ZT_0 is given by the square of this mixed noise divided by the product of charge noise by heat noise. The fact to consider the auto-correlations in the same reservoir, or the cross-correlations between distinct reservoir leads to the same ratio of noises in that regime. It is no longer the case in the high voltage regime, where r_{LL} or r_{RR} and r_{LR} take different values: because of Cauchy-Schwarz inequality, r_{LL} and r_{RR} stay smaller than one whereas there is not limitation for r_{LR}. Moreover, the auto-ratios show asymmetry for the QD arising from distinct heat noises in the two reservoirs. The cross-ratio r_{LR}, introduced for the first time in this paper, deserves to be studied on an equal footing than r_{LL} and r_{RR} since it measures how heat current in one reservoir and charge current in the other are related to each other. Knowing that the figure of merit is no longer connected to thermoelectrical efficiency in non-linear regime,[23] it is needed to find a new parameter which informs about efficiency: theses ratios of noises are a possible track to further validate.

Acknowledgments

A.C. thanks Marine Guigou for interesting discussions.

Appendix A: QPC noises in the high voltage regime

Taking $T_L = T_R = 0$, the integrals in the expressions of the noises of Eqs. (37), (38), (39), (40), (41) and (42) can be performed analytically. We obtain for the auto-correlators:

$$\mathcal{S}^{ee}_{LL} = \frac{e^2}{h}\mathrm{sign}(V)\left[-\frac{eV\Gamma^2}{2[\Gamma^2+(eV/2)^2]} + \Gamma\arctan\left(\frac{eV}{2\Gamma}\right)\right], \quad \text{(A1)}$$

$$\mathcal{S}^{eh}_{LL} = \frac{e}{h}\mathrm{sign}(V)\left[\frac{(eV\Gamma)^2}{4[\Gamma^2+(eV/2)^2]} - \frac{eV\Gamma}{2}\arctan\left(\frac{eV}{2\Gamma}\right)\right], \quad \text{(A2)}$$

$$\mathcal{S}^{eh}_{RR} = \frac{e}{h}\mathrm{sign}(V)\left[-\frac{(eV\Gamma)^2}{4[\Gamma^2+(eV/2)^2]} + \frac{eV\Gamma}{2}\arctan\left(\frac{eV}{2\Gamma}\right)\right], \quad \text{(A3)}$$

$$\mathcal{S}^{hh}_{LL} = \frac{1}{h}\mathrm{sign}(V)\left[\frac{eV\Gamma^2}{8}\frac{(eV)^2+12\Gamma^2}{\Gamma^2+(eV/2)^2} + \frac{\Gamma}{4}[(eV)^2-12\Gamma^2]\arctan\left(\frac{eV}{2\Gamma}\right)\right], \quad \text{(A4)}$$

$$\mathcal{S}^{hh}_{RR} = \mathcal{S}^{hh}_{LL}, \quad \text{(A5)}$$

and for the cross-correlators:

$$\mathcal{S}^{ee}_{LR} = -\mathcal{S}^{ee}_{LL}, \quad \text{(A6)}$$

$$\mathcal{S}^{he}_{LR} = -\mathcal{S}^{eh}_{LL}, \quad \text{(A7)}$$

$$\mathcal{S}^{eh}_{LR} = -\mathcal{S}^{eh}_{RR}, \quad \text{(A8)}$$

$$\mathcal{S}^{hh}_{LR} = -\frac{1}{h}\mathrm{sign}(V)\left[\frac{3\Gamma^2 eV}{2} - \frac{\Gamma}{4}[(eV)^2+12\Gamma^2]\arctan\left(\frac{eV}{2\Gamma}\right)\right]. \quad \text{(A9)}$$

Appendix B: QD noises in the high voltage regime

For the QD, Eqs. (37), (38), (39), (40), (41) and (42) give at zero temperature for the auto-correlators:

$$\mathcal{S}^{ee}_{LL} = \frac{e^2}{h}\mathrm{sign}(V)\sum_{\pm}\left[\pm\frac{\Gamma^2}{2}\frac{\epsilon_0 \mp eV/2}{(\epsilon_0 \mp eV/2)^2+\Gamma^2} \mp\frac{\Gamma}{2}\arctan\left(\frac{\epsilon_0 \mp eV/2}{\Gamma}\right)\right], \quad \text{(B1)}$$

$$\mathcal{S}^{eh}_{LL} = \frac{e}{h}\mathrm{sign}(V)\sum_{\pm}\left[\frac{\Gamma^2 eV}{4}\frac{\epsilon_0 \mp eV/2}{(\epsilon_0 \mp eV/2)^2+\Gamma^2} \mp\frac{\Gamma\epsilon_0}{2}\arctan\left(\frac{\epsilon_0 \mp eV/2}{\Gamma}\right) \pm\frac{\Gamma^2}{2}\ln[(\epsilon_0 \mp eV/2)^2+\Gamma^2]\right] - \frac{V}{2}\mathcal{S}^{ee}_{LL}, \quad \text{(B2)}$$

$$\mathcal{S}^{eh}_{RR} = \frac{e}{h}\mathrm{sign}(V)\sum_{\pm}\left[\frac{\Gamma^2 eV}{4}\frac{\epsilon_0 \mp eV/2}{(\epsilon_0 \mp eV/2)^2+\Gamma^2} \mp\frac{\Gamma\epsilon_0}{2}\arctan\left(\frac{\epsilon_0 \mp eV/2}{\Gamma}\right) \pm\frac{\Gamma^2}{2}\ln[(\epsilon_0 \mp eV/2)^2+\Gamma^2]\right] + \frac{V}{2}\mathcal{S}^{ee}_{RR} \quad \text{(B3)}$$

$$= \mathcal{S}^{eh}_{LL} + V\mathcal{S}^{ee}_{LL}, \quad \text{(B4)}$$

$$\mathcal{S}^{hh}_{LL} = \frac{\mathrm{sign}(V)}{h}\sum_{\pm}\Bigg[\frac{\Gamma^2 eV}{2} \pm\frac{\Gamma^2}{2}\frac{\epsilon_0^2(\epsilon_0\mp eV/2)+\Gamma^2(\epsilon_0\pm eV/2)}{(\epsilon_0\mp eV/2)^2+\Gamma^2} \mp\frac{\Gamma(\epsilon_0^2-3\Gamma^2)}{2}\arctan\left(\frac{\epsilon_0\mp eV/2}{\Gamma}\right) \pm\Gamma^2\epsilon_0\ln[(\epsilon_0\mp eV/2)^2+\Gamma^2]\Bigg] -V\mathcal{S}^{eh}_{LL}-\frac{V^2}{4}\mathcal{S}^{ee}_{LL}\ , \quad \text{(B5)}$$

$$\mathcal{S}^{hh}_{RR} = \frac{\mathrm{sign}(V)}{h}\sum_{\pm}\Bigg[\frac{\Gamma^2 eV}{2} \pm\frac{\Gamma^2}{2}\frac{\epsilon_0^2(\epsilon_0\mp eV/2)+\Gamma^2(\epsilon_0\pm eV/2)}{(\epsilon_0\mp eV/2)^2+\Gamma^2} \mp\frac{\Gamma(\epsilon_0^2-3\Gamma^2)}{2}\arctan\left(\frac{\epsilon_0\mp eV/2}{\Gamma}\right) \pm\Gamma^2\epsilon_0\ln[(\epsilon_0\mp eV/2)^2+\Gamma^2]\Bigg] +V\mathcal{S}^{eh}_{RR}-\frac{V^2}{4}\mathcal{S}^{ee}_{RR} \quad \text{(B6)}$$

$$= \mathcal{S}^{hh}_{LL}+2V\mathcal{S}^{eh}_{LL}+V^2\mathcal{S}^{ee}_{LL}\ , \quad \text{(B7)}$$

and for the cross-correlators:

$$\mathcal{S}^{ee}_{LR} = -\mathcal{S}^{ee}_{LL}\ , \quad \text{(B8)}$$

$$\mathcal{S}^{he}_{LR} = -\mathcal{S}^{eh}_{LL}\ , \quad \text{(B9)}$$

$$\mathcal{S}^{eh}_{LR} = -\mathcal{S}^{eh}_{RR}\ , \quad \text{(B10)}$$

$$\mathcal{S}^{hh}_{LR} = -\frac{\mathrm{sign}(V)}{h}\sum_{\pm}\Bigg[\frac{\Gamma^2 eV}{2} \pm\frac{\Gamma^2}{2}\frac{\epsilon_0^2(\epsilon_0\mp eV/2)+\Gamma^2(\epsilon_0\pm eV/2)}{(\epsilon_0\mp eV/2)^2+\Gamma^2} \mp\frac{\Gamma(\epsilon_0^2-3\Gamma^2)}{2}\arctan\left(\frac{\epsilon_0\mp eV/2}{\Gamma}\right) \pm\Gamma^2\epsilon_0\ln[(\epsilon_0\mp eV/2)^2+\Gamma^2]\Bigg] -\frac{V^2}{4}\mathcal{S}^{ee}_{LR}\ . \quad \text{(B11)}$$

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